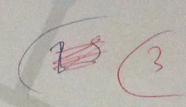
University of Jordan Computer engineering department Digital Electronics Quiz #1



Name:

0/47 All Me / 12 number: 0100576

Assume the following:

V_{BE} at the edge between OFF and active = 0.7 V

V_{BE} at the edge between active and saturation = 0.8 V

 V_{CE} at the edge between active and saturation is = 0.4 V

 V_{CE} in comfortable saturation is = 0.2

B of the transistor = 200

 $R_{C} = 2.3 \text{ K}$ $R_{B} = 2 \text{ K}$

 $V_{cc} = 5 V$

P1 the input voltage at which the transfer characteristic starts to drop

P2 the input voltage at which the transfer characteristic ends dropping

The gate is cascaded (connected to other similar gate).

Drawn is the basic RTL gate.

The logic function of this gate expressed in terms of its inputs is:

Fill the table with (no change, increase, decrease, shift right, shift left) upon the given introduced change:

introduced change	Fan-out	Voltage swing	L P1	P2	Switching delay 0 → 1	Switching delay 1→ 0
	1 de	decrea	se.	UC		N
ncrease R _c	intimely	6-1308	no change	eshill cel	- degrase	decien
Increase V _{cc}	no chan	ge noch	g noo	haral,	1	
The state of the s	30	, ×	100	marge L	decon	e ma

University of Jordan Computer engineering department Digital Electronics Quiz #1



Name: ルズーツリッションシン

number: 0100729

Assume the following:

 $\ensuremath{V_{\text{BE}}}$ at the edge between OFF and active = 0.7 \ensuremath{V}

 V_{BE} at the edge between active and saturation = 0.8 V

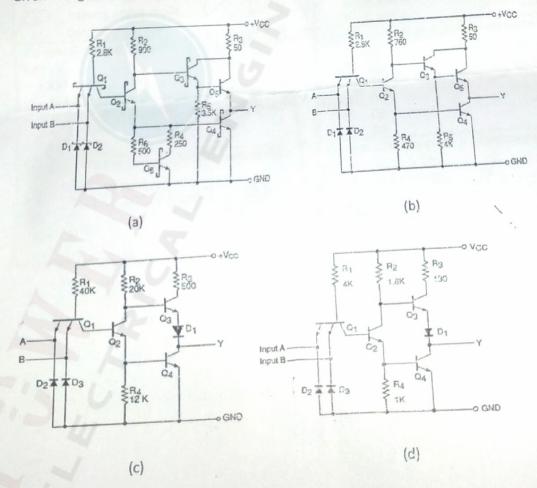
 V_{CE} at the edge between active and saturation is = 0.4 V

 V_{CE} in comfortable saturation is = 0.2

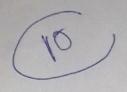
B of the transistor = 200

Vcc =5 V

Given 4 diagrams for TTL gates.



The gate that has a passive pull-down is:	The slowest gate is:
The gate that has a passive part	1. A
(a) All	2. B
(b) A and b	3DC
C C and d	4. D
(d) None	4. 0
C	
The gate with the most power dissipation is:	The gate with an active pull-down is:
(A)	1 A
B. B	2) B
C. C	3) C (/ (1)
4	4) D
D. D	40
the state of its in:	Gates with totem pole are:
When all inputs are Low transistor Q1 is in:	ALL I
i. OFF mode	b. None
ii. Forward Active mode	
Inverse active mode	c. A and B.
iv. Saturation mode	d. C and D
If a specifications reads that IiL = - 1.4 mA then it is	The transistor that will never saturate is:
for:	1. Q1
1) A	2. Q2
2) B	3. Q3
3) C	4. Q4
(4) D	5. Q5
(5) A or B	6. Q6
The gate with the best shape I/O characteristic:	Fan out of these gates is calculated when:
II. B	A. Input is Low
	B. Input is High
	Output is Low
iv. D	Output is High
	,



University of Jordan Computer engineering department Digital Electronics Quiz #3

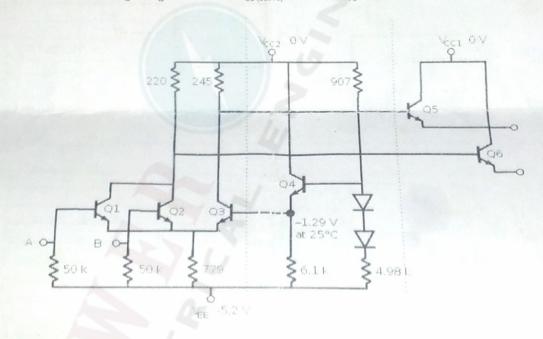
Name: Glar all us light us

number: 0100 576

ECL is an acronym of | Emitter-Coupled Logic

The main advantage of ECL is in its:	Fan out
	Noise margin
	Power dissipation
	Speed

Given the following ECL gate. Assume $V_{BE (active)} = 0.75 \text{ V}$ $h_{FE} = 100$



Answer the following questions:

The logic function at Vol (in terms of A and B) is:	A + B
The logic function at V _{o2} (in terms of A and B) is:	(A + B)'
The logic low level is:	- 1.74
The logic high level is:	- 0.75

University of Jordan Computer engineering department Digital Electronics

Quiz #3 number: 0100729

Name: 18/12/2081/1/20

0	A	В	C	F	VDD VDD 00 11 11
0	0	0	- 0	+	T. J. Col Toll
80	0	0	1	+	C-d. ?!
0	0	1	0	1	A-d In Co
2	0	1	1	1	
2	1	0	. 0	1	B-0 + 2
0	1	0	1	0) (//
6	1	1	0	0	- IF /
0	1	1	1	0	D-q_
1	0	9	0	0	F
1	The function	n is	1	0	
1	20	1	0	0	12 1
1	0	1	1	0	
1	1	0	0	0	B-I C-I
1	1	0	1	10	
1	1	1	0	0	
1	,	,	1 1	10	
T	A	1	В	F	V _{DD}
	0		0	dia	bod 4bog
	0		1	CD	Joeq Joea
	1		0	0	
	1	1	1	1	la-d b-b
	0		0		Π Γ .
	0		1		
	1		0		\bar{a}
	1		1		la h